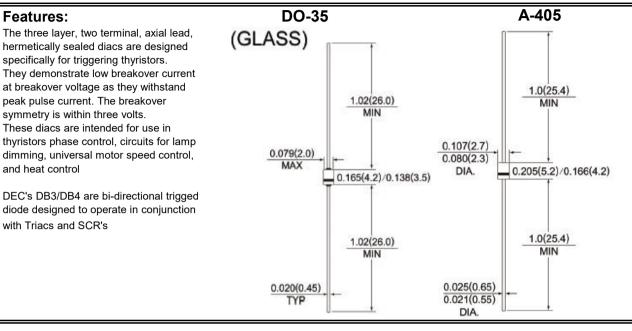


DB3/DB4

SIGNAL BIDIRECTIONALDIAC POWER DISSIPATION 150 mW



Absolute Ratings (Limiting Values)

Symbols	Parameters		Value	Units	
Symbols			DB3	DB4	Units
Pc	Power Dissipation on Printed Circuit(L=10mm)	TA=50℃	150		mW
ITRM	Repetitive Peak on-state Current	tp=10µs F=100Hz	2.0	2.0	А
TSTG/TJ	Storage and Operating Junction Temperature		-40 to +125/-40 to 110		Ĉ

Electrical characteristics

Symbols	Parameters	Test Conditions		Value		Units
Symbols	Parameters			DB3	DB4	Units
VBO	Breakover Voltage (Note 2)	C=22nF(Note2) See diagram 1	Min	28.0	35.0	V
			Тур	32.0	40.0	
			Max	36.0	45.0	
+VBO - - VBO	Breakover Voltage Symmetry	C=22nF(Note2) See diagram 1	Max	±3		V
±△V	Dynamic Breakover Voltage (Note 1)	△I=(IBO to IF=10mA)	Min	5		V
VO	Output Voltage (Note 1)	See diagram 2	Min	5		V
IBO	Breakover Current (Note 1)	C=22nF(Note2)	Max	100		μA
tr	Rise Time (Note 1)	See diagram 3	Тур	1.5		μS
IB	Leakage Current (Note 1)	VB=0.5 VBO max see diagram 1	Max	10		μA

Notes:(1) Electrical characteristics applicable in both forward and reverse directions

(2) Connected in parallel with the devices

RATINGS AND CHARACTERISTIC CURVES DB3 / DB4

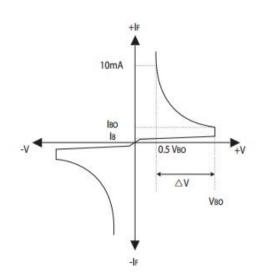
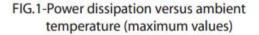
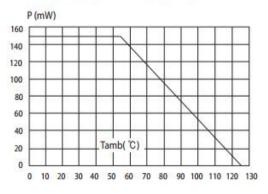
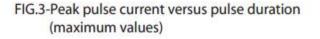


DIAGRAM 1 : Current-voltage characteristics







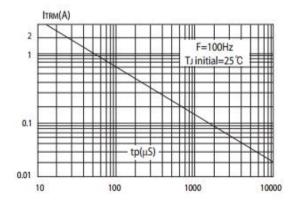
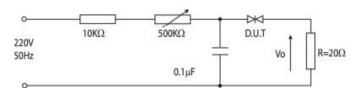
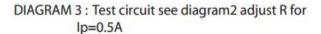


DIAGRAM 2 : Test circuit for output voltage





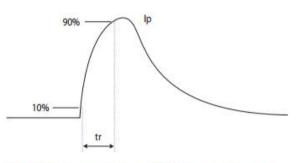


FIG.2-Relative variation of VBO versus junction temperature (typical values)

